

# Ingo Tischer

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2358178/publications.pdf>

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29  
papers

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1163117

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1058476

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29  
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docs citations

29  
times ranked

321  
citing authors



#	ARTICLE	IF	CITATIONS
19	Stacking fault emission in GaN: Influence of n-type doping. Journal of Applied Physics, 2016, 119, .	2.5	5
20	Three-dimensional cathodoluminescence characterization of a semipolar GaInN based LED sample. Journal of Applied Physics, 2017, 121, .	2.5	5
21	Evidence of terbium and oxygen co-segregation in annealed AlN:Tb. Applied Physics Letters, 2017, 110, .	3.3	5
22	INGAN/GAN based semipolar green converters. Journal of Crystal Growth, 2013, 370, 120-123.	1.5	3
23	Coaxial InGaN epitaxy around GaN micro-tubes: Tracing the signs. Journal of Crystal Growth, 2013, 370, 319-322.	1.5	3
24	Suppression of gallium inhomogeneity in ZnO nanostructures on GaN using seed layers. Materials Letters, 2012, 83, 31-34.	2.6	1
25	Optical Properties of ZnO/GaN/InGaN Core-Shell Nanorods. Japanese Journal of Applied Physics, 2013, 52, 075201.	1.5	1
26	Measurement of the diffusion length and the lifetime of free excitons in gallium nitride using cathodoluminescence under different conditions of luminescence excitation. Journal of Surface Investigation, 2015, 9, 839-843.	0.5	1
27	Crystal quality improvement of semipolar (20-21) GaN on patterned sapphire substrates by in-situ deposited SiN mask. , 2014, , .		0
28	(Invited) Large Area Semipolar GaN Grown on Foreign Substrates. ECS Transactions, 2014, 61, 101-107.	0.5	0
29	Composition analysis of coaxially grown InGaN multi quantum wells using scanning transmission electron microscopy. Journal of Applied Physics, 2016, 119, 175701.	2.5	0